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Question Paper Code: 90176

B.E./B.Tech. DEGREE EXAMINATIONS, NOVEMBER/DECEMBER 2019 Third Semester

Biomedical Engineering EC8353 – ELECTRON DEVICES AND CIRCUITS

(Common to Computer and Communication Engineering/Electrical and Electronics Engineering/Electronics and Instrumentation Engineering/Instrumentation and Control Engineering/Robotics and Automation Engineering)
(Regulations 2017)

Time: Three Hours

Maximum: 100 Marks

Answer ALL questions

PART – A

 $(10\times2=20 \text{ Marks})$

- 1. Why the depletion layer is very thin in zener diode?
- 2. What is a rectifier and mention its types?
- 3. How a FET is used as a voltage variable resistor?
- 4. What is meant by "thermal runaway" in a transistor and how it can be avoided?
- 5. Mention the significance of coupling and bypass capacitor on bandwidth of amplifiers.
- 6. State Miller's theorem.
- 7. A tuned circuit has a resonant frequency of 1600 kHz and a bandwidth of 10 kHz. Calculate the value of the Q factor.
- 8. What is the impact of crossover distortion in an amplifier?
- 9. Which type of feedback circuit increases gain of an amplifier?
- 10. Draw the equivalent circuit of Crystal oscillator.

(6)

PART - B

(5×13=65 Marks)

- 11. a) i) Draw and explain the VI characteristics of PN junction diode. (5)
 - ii) Derive the expression of the space charge or transition capacitance of PN diode under reverse bias with neat diagram. (8)

(OR)

- b) With neat sketches, explain the operation of a Half Wave rectifier circuit and also derive the expression for Transformer Utilization Factor (TUF), Peak Inverse Voltage (PIV) and efficiency.
- 12. a) i) With neat sketches, explain the input and output characteristics of an Emitter Follower.
 - ii) Enumerate the selection of Q point for transistor bias circuit and discuss the limitations on the output voltage swing. (7)

(OR)

- b) Describe the construction and working of UJT with its equivalent circuit and VI characteristics.
- 13. a) Explain about CC amplifier and derive the expression for h parameters of the same. Also derive the expression for gain, input impedance and output impedance of CC amplifier.

(OR)

- b) Explain about CS amplifier and derive the expression for gain, input impedance and output impedance and also draw its small signal equivalent circuit.
- 14. a) Draw the circuit of emitter coupled BJT differential amplifier and derive the expressions for differential gain, common mode gain and CMRR.

(OR)

b) If Class C Tuned amplifier has $R_L = 6k\Omega$ and required tank circuit Q = 80. Estimate the values of L and C of the tank circuit. Assume $V_{CC} = 20$ V, resonant frequency as 5 MHz and worst case power dissipation as 20 mW.

- 15. a) With a neat block diagram, explain the operation of following feedback amplifiers.
 - i) Voltage series feedback amplifier (6)
 - ii) Current shunt feedback amplifier (7)

(OR)

b) With neat diagram, examine the Wein bridge oscillator and derive an expression for frequency of oscillation.

 $PART - C \qquad (1 \times 15 = 15 \text{ Marks})$

- 16. a) i) In a Colpitts oscillator, $C_1 = C_2 = C$ and $L = 100 \times 10^{-6}$ H. The frequency of oscillation is 500 kHz. Determine the value of C. (5)
 - ii) In Colpitts oscillator, the desired frequency is 500 kHz. Estimate the value of L by assuming C = 1000 pF.
 - iii) A 1 mH inductor is available. Choose the capacitor values in a Colpitts oscillator so that f = 1 MHz and feedback factor is 0.25.

(OR)

b) For a CB amplifier driven by voltage source of internal resistance $R_a = 1.2 \ K\Omega$. The load impedance is $R_L = 1 k\Omega$. The h parameters are $h_{ib} = 22\Omega$, $h_{cb} = 3 \times 10^{-4}$, $h_{fb} = -0.98$ and $h_{ob} = 0.5 \text{A/V}$. Estimate the current gain Ai, Input impedance Ri, voltage gain Av, overall current gain Ais, overall voltage gain Avs and output impedance Zo.